

IN THE SPECIFICATION:

Please amend page 12, lines 12-17 of the specification as originally filed as follows:

An n-type semiconductor film 105 is formed over a semiconductor film 104. As an n-type impurity element, arsenic [(Ar)](As) and phosphorus (P) can be used. In case of forming an n-type semiconductor film, an n-type (n+) silicon film can be formed by the grow discharge decomposition of a mixed gas of SiH₄, H₂, and PH₃ (phosphine) using plasma CVD. Instead of the n-type semiconductor film 105, a semiconductor film containing p-type impurity elements such as boron (B) can be formed.